

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

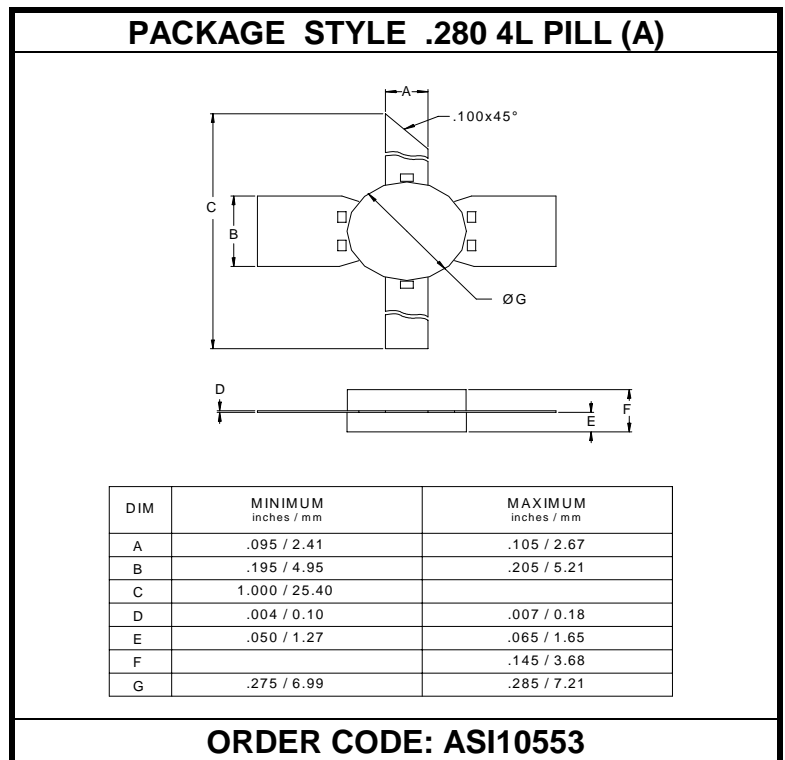
The **ASI AVD002P** is Designed for Class C, DME/TACAN Applications up to 1150 MHz.

FEATURES:

- Class C Operation
- $P_G = 9.0$ dB at 2.0 W/1150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	250 mA
V_{CC}	37 V
P_{DISS}	10 W @ $T_C \leq 100$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	10 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	45			V
BV_{CER}	$I_C = 5.0$ mA $R_{BE} = 10$ Ω	45			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CES}	$V_{CE} = 35$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ A	30		300	---
P_G	$V_{CC} = 35$ V $P_{OUT} = 2.0$ W $f = 1025 - 1150$ MHz	9.0			dB
η_c		35			%